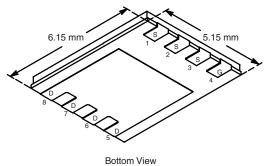


Vishay Siliconix

N-Channel 30-V (D-S) MOSFET

PRODUCT SUMMARY				
V _{DS} (V)	R_{DS(on)} (Ω)	I _D (A)	Q _g (Typ.)	
30	0.0042 at V_{GS} = 10 V	23	30.5	
	0.0059 at V _{GS} = 4.5 V	20	30.5	





Ordering Information: Si7358ADP-T1-E3 (Lead (Pb)-free)

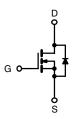
Si7358ADP-T1-GE3 (Lead (Pb)-free and Halogen-free)

FEATURES

- Halogen-free available
- TrenchFET[®] Power MOSFET
- Optimized for "Low Side" Synchronous Rectifier Operation
- New Low Thermal Resistance PowerPAK[®] Package with Low 1.07 mm Profile
- 100 % R_g Tested

APPLICATIONS

- DC/DC Converters
- Synchronous Rectifiers



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS T_{μ}	, = 25 °C, unle	ss otherwise n	oted		
Parameter		Symbol	10 s	Steady State	Unit
Drain-Source Voltage		V _{DS}	30		V
Gate-Source Voltage		V _{GS}	± 20		v
Continuous Drain Current (T _{.1} = 150 °C) ^a	T _A = 25 °C	I _D	23	14	
Continuous Drain Current $(1) = 150^{\circ}$ C)	T _A = 70 °C		18	11	
Pulsed Drain Current (10 µs Pulse Width)		I _{DM}	60		А
Continuous Source Current (Diode Conduction) ^a		۱ _S	4.5	1.6	
Avalanche Current	L = 0.1 mH	I _{AS}	50		
Maximum Power Dissipation ^a	T _A = 25 °C	P _D	5.4	1.9	W
	T _A = 70 °C		3.4	1.2	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 150		°C
Soldering Recommendations (Peak Temperature) ^{b, c}			260		0

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Mauinnum lunation to Amhianta	t ≤ 10 s	R _{thJA} R _{thJC}	18	23	
Maximum Junction-to-Ambient ^a	Steady State		50	65	°C/W
Maximum Junction-to-Case (Drain)	Steady State		1.0	1.5	

Notes:

a. Surface Mounted on 1" x 1" FR4 board.

b. See Solder Profile (http://www.vishay.com/ppg?73257). The PowerPAK SO-8 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.

c. Rework Conditions: manual soldering with a soldering iron is not recommended for leadless components.



Si7358ADP

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Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
Static			•				
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_D = 250 \ \mu A$	1.0		3.0	V	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 V, V_{GS} = \pm 20 V$			± 100	nA	
Zero Gate Voltage Drain Current	1	$V_{DS} = 30 \text{ V}, \text{ V}_{GS} = 0 \text{ V}$ $V_{DS} = 30 \text{ V}, \text{ V}_{GS} = 0 \text{ V}, \text{ T}_{J} = 55 \text{ °C}$			1	μA	
	DSS				5		
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \ge 5 \text{ V}, V_{GS} = 10 \text{ V}$	30			А	
Drain-Source On-State Resistance ^a	Б	$V_{GS} = 10 \text{ V}, \text{ I}_{D} = 23 \text{ A}$		0.0032	0.0042	-	
	R _{DS(on)}	$V_{GS} = 4.5 \text{ V}, \text{ I}_{D} = 20 \text{ A}$		0.0045	0.0059	Ω	
Forward Transconductance ^a	9 _{fs}	$V_{DS} = 15 \text{ V}, I_{D} = 23 \text{ A}$		90		S	
Diode Forward Voltage ^a	V _{SD}	$I_{S} = 4.5 \text{ A}, V_{GS} = 0 \text{ V}$		0.75	1.1	V	
Dynamic ^b	1. J.						
Input Capacitance	C _{iss}			4650		pF	
Output Capacitance	C _{oss}	V_{DS} = 15 V, V_{SS} = 0 V, f = 1 kHz		880			
Reverse Transfer Capacitance	C _{rss}			390			
Total Gate Charge	Qg			30.5	40		
Gate-Source Charge	Q _{gs}	V_{DS} = 15 V, V_{GS} = 4.5 V, I_D = 23 A		12.5		nC	
Gate-Drain Charge	Q _{gd}			10			
Gate Resistance	Rg		0.5	1.0	1.5	Ω	
Turn-On Delay Time	t _{d(on)}			21	35		
Rise Time	t _r	V_{DD} = 15 V, R_L = 15 Ω		10	20	. ns	
Turn-Off Delay Time	t _{d(off)}	$I_D \cong$ 1 A, V_{GEN} = 10 V, R_G = 6 Ω		83	130		
Fall Time	t _f			27	45		
Source-Drain Reverse Recovery Time	t _{rr}	I _F = 2.9 A, di/dt = 100 A/μs		50	80		

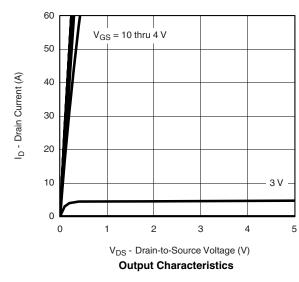
Notes:

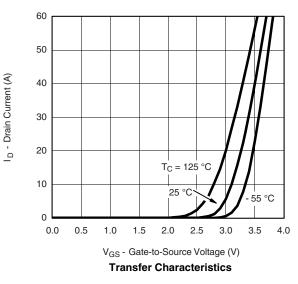
a. Pulse test; pulse width \leq 300 $\mu s,$ duty cycle \leq 2 %.

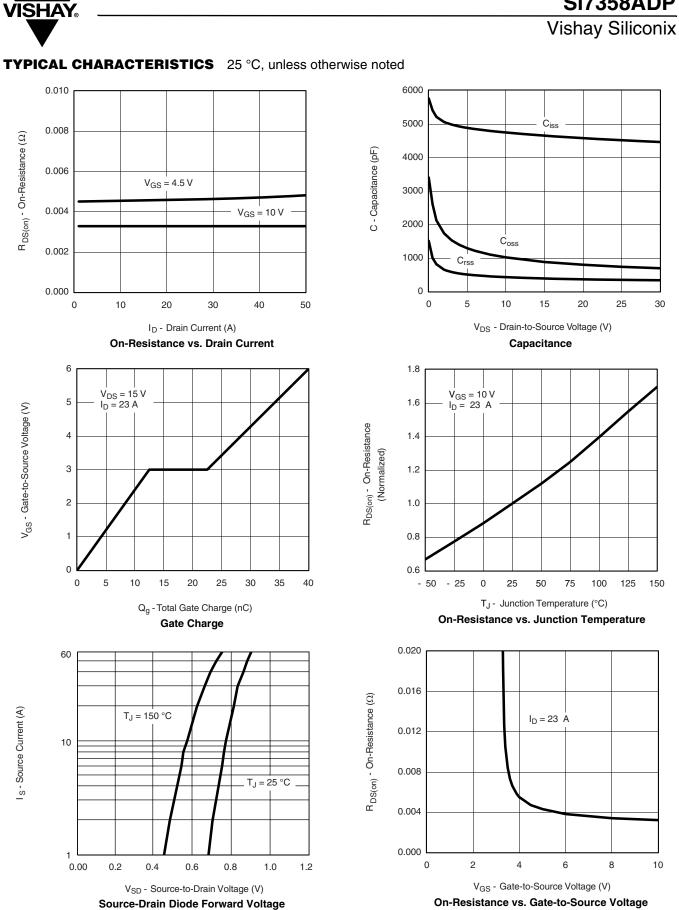
b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted





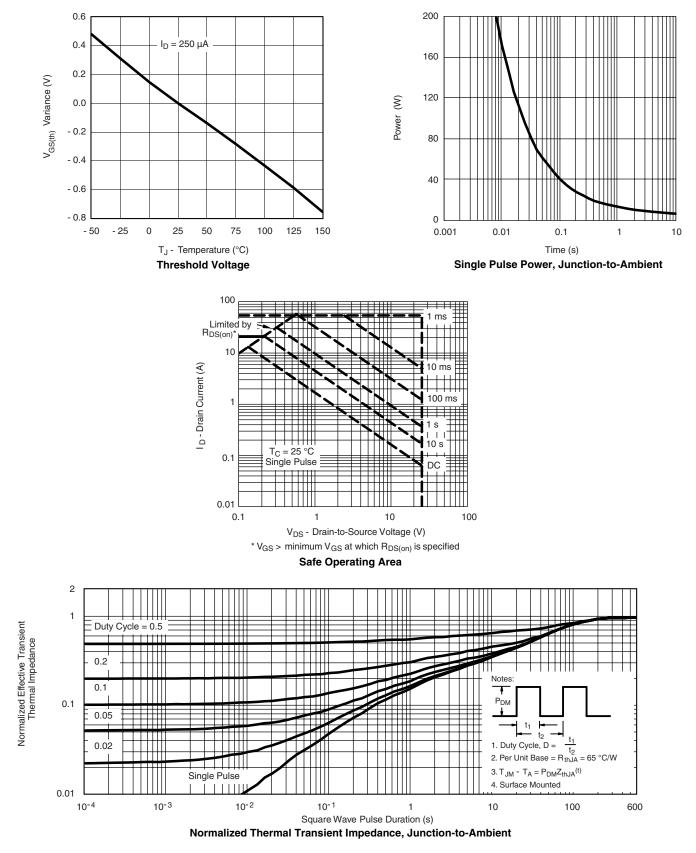


Document Number: 73161 S-80438-Rev. E, 03-Mar-08 Si7358ADP

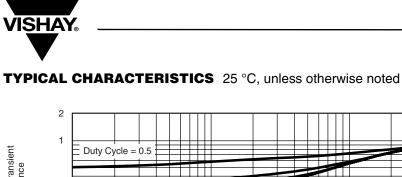
Si7358ADP

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TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted







 $\mathsf{T}_{\mathsf{Super Wave Pulse Duration (s)}}^{\mathsf{T}}$

Normalized Thermal Transient Impedance, Junction-to-Case

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see http://www.vishay.com/ppg?73161.

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